

DOCUMENT CHANGE REQUEST

DCR number 1151 Changes required for: General Originator: Steve Jeffery

Date: 2018/05/08 Date sent: 2018/03/20 Organisation: ESCC Executive

Status: IMPLE	EMENTED				
Title:	Matched Dual Transistors NPN, based on types 2N2919/2N2920 and 2N2920A				
Number:	5207/002	Issue:	8		
Other documen	ts affected:				
5207/005-5					
Page:					
13 of 5207/005; 13 & 14 of 5207/002.					
Paragraph:					
2.4.2 of 5207/005; 2.4.1 & 2.4.2 of 5207/002.					
Original wording	j :				
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Proposed wording:					
In 5207/005 Issue 5, Para. 2.4.2, the units of the Base-Emitter Voltage Differential Change Characteristic [both (VBE1-VBE2)Tamb 1 and (VBE1-VBE2)Tamb 2] are "mV". These shall be corrected to "µV" (i.e. microvolts).					
In 5207/002 Issue 7, Para. 2.4.1, the units of the Base-Emitter Voltage Differential Characteristic (specifically VBE1-VBE2 1 and VBE1-VBE2 2) are "µV". These shall be corrected to "mV" (i.e. millivolts).					
In 5207/002 Issue 7, Para. 2.4.2, Forward-Current Transfer Ratio Comparison Characteristic, the Test Condition "IC = 100mA " shall be corrected to "IC = $100\mu\text{A}$ ".					
Justification:					

This DCR is raised to correct editorial errors, notified by the ESA Qualified Manufacturer STMicroelectronics, which

occurred during the update to these two Detail Specifications' current Issues.

Attachments:		
N/A		
Modifications:		
N/A		
Approval signature:		
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Date signed:		
2018-05-08		